

BUK9209-40B

N-channel TrenchMOS logic level FET Rev. 03 — 15 June 2010

Product data sheet

Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 185 °C rating

1.3 Applications

- 12 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C		-	-	40	V
I _D	drain current	$V_{GS} = 5 \text{ V}; T_{mb} = 25 \text{ °C};$ see Figure 1; see Figure 3	<u>[1]</u>	-	-	75	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	167	W
Static char	acteristics						
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$		-	6.2	7	mΩ
	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 11; see Figure 12		-	7.6	9	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 75$ A; $V_{sup} \le 40$ V; $R_{GS} = 50$ Ω ; $V_{GS} = 5$ V; $T_{j(init)} = 25$ °C; unclamped	-	-	242	mJ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 32 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	12	-	nC

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9209-40B	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C		-	-	40	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	40	V
V_{GS}	gate-source voltage			-15	-	15	V
I _D	drain current	$T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 5 \text{V}; \text{see } \frac{\text{Figure 1}}{\text{see } \frac{\text{Figure 3}}{\text{Figure 3}}};$	<u>[1]</u>	-	-	99	Α
			[2]	-	-	75	Α
		$T_{mb} = 100 ^{\circ}C; V_{GS} = 5 V; \text{see } \underline{\text{Figure 1}}$	<u>[1]</u>	-	-	70	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; t_p ≤ 10 μs; pulsed; see Figure 3		-	-	396	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	167	W
T _{stg}	storage temperature			-55	-	185	°C
Tj	junction temperature			-55	-	185	°C
Source-drain	diode						
Is	source current	T _{mb} = 25 °C	[1]	-	-	99	Α
			[2]	-	-	75	Α
I _{SM}	peak source current	t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C		-	-	396	Α
Avalanche rug	ggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω ; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	242	mJ

^[1] Current is limited by power dissipation chip rating.

^[2] Continuous current is limited by package.

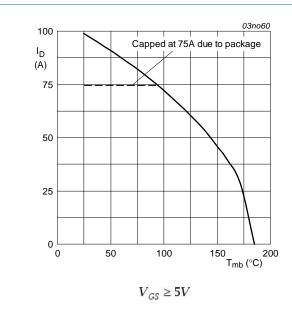


Fig 1. Continuous drain current as a function of mounting base temperature

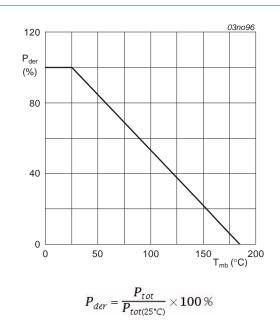
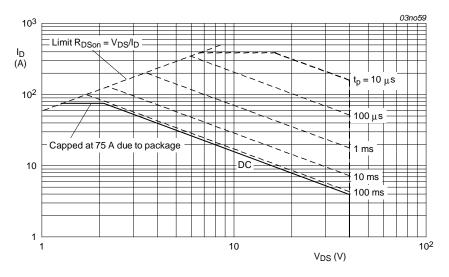


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25^{\circ}C; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	71.4	-	K/W

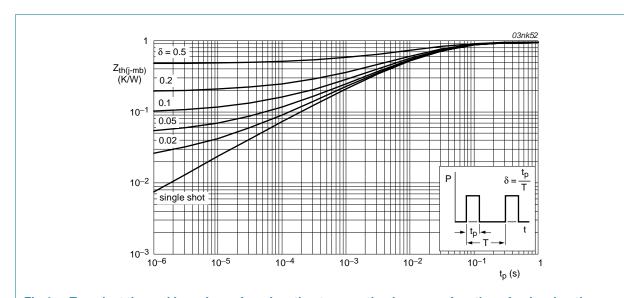


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics	Conditions	N # !	Ti	Mari	11
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	40	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 10</u>	1.1	1.5	2	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 185$ °C; see <u>Figure 10</u>	0.4	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 10</u>	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 185 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.02	1	μΑ
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 15 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -15 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	10	mΩ
	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 185 °C;$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	17.5	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	6.2	7	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11; see Figure 12	-	7.6	9	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$	-	32	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 13</u>	-	7	-	nC
Q_{GD}	gate-drain charge		-	12	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	2714	3619	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	481	577	pF
C _{rss}	reverse transfer capacitance		-	209	286	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	29	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	106	-	ns
t _{d(off)}	turn-off delay time		-	108	-	ns
t _f	fall time		-	89	-	ns
L _D	internal drain inductance	measured from drain to center of die ; $T_i = 25 ^{\circ}\text{C}$	-	2.5	-	nΗ
L _S	internal source inductance	measured from source lead to source bond pad; $T_j = 25$ °C	-	7.5	-	nΗ
Source-di	ain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	57	-	ns
Qr	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	47	_	nC

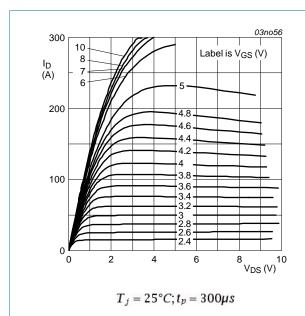


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

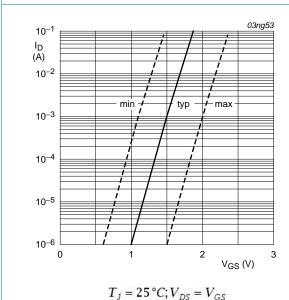
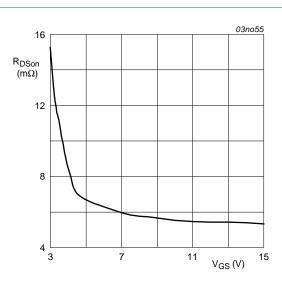


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; I_D = 25A$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

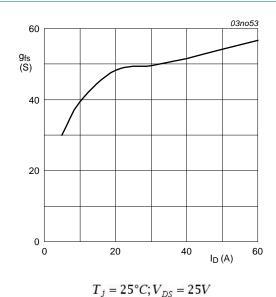


Fig 8. Forward transconductance as a function of drain current; typical values

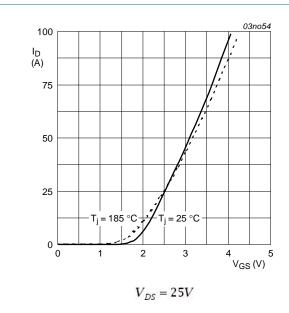


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

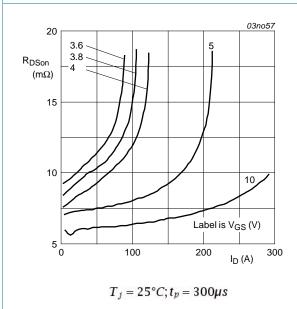
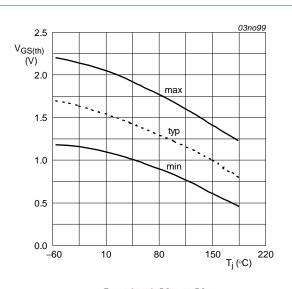


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 1mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

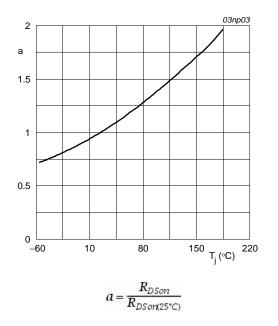


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

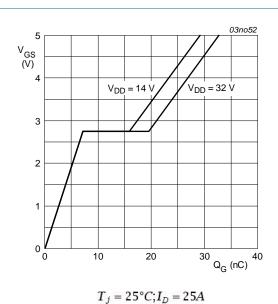
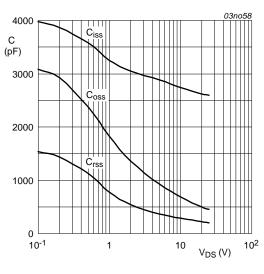


Fig 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

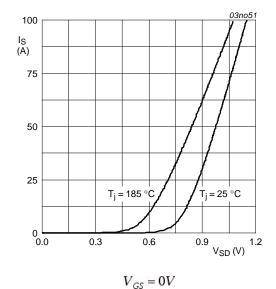


Fig 15. Source current as a function of source-drain voltage; typical values

7. Package outline

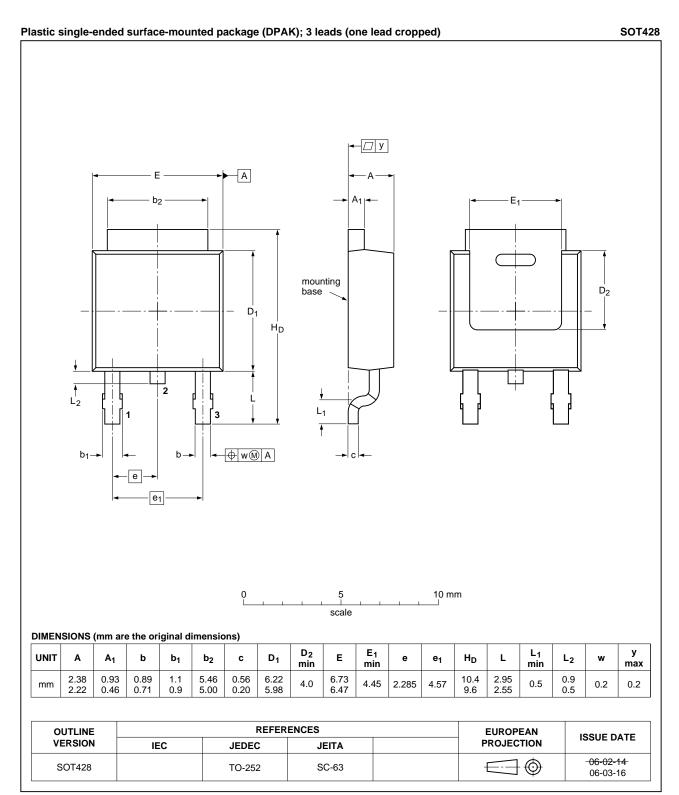


Fig 16. Package outline SOT428 (DPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BUK9209-40B v.3	20100615	Product data sheet	-	BUK9209-40B v.2			
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 						
	 Legal texts have been adapted to the new company name where appropriate. 						
BUK9209-40B v.2 (9397 750 12234)	20031212	Product data	-	-			

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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N-channel TrenchMOS logic level FET

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